This listing of claims will replace all prior versions, and listings, of claims in the application: Listing of claims:

- 1. (Canceled)
- 2. (Canceled)
- 3. (Canceled)
- 4. (Currently amended) An etching solution according to Claim <u>17</u> 4, comprising a solvent mixture consisting essentially of ethylene glycol and glycerol in a mixing ratio of from 1:10 to 10:1.
- 5. (Currently amended) An etching solution according to Claim 17 +, comprising a solvent mixture consisting essentially of ethylene glycol and glycerol in a mixing ratio of from 1:5 to 5:1.
- 6. (Canceled)
- 7. (Currently amended) An etching solution according to Claim <u>17</u> 1, comprising a mixture of high-purity individual components.
- 8. (Withdrawn) A method for the selective etching of doped silicate layers comprising treating said doped silicate layers with an etching solution according to Claim 1.
- 9. (Withdrawn) A method according to claim 8, wherein said doped silicate is boron doped glass.
- 10. (Withdrawn) A method according to claim 8, wherein said doped silicate is phosphorous doped glass.
- 11. (Withdrawn) A method according to claim 8, wherein said doped silicate is boron-phosphorous doped glass.

- 12. (Withdrawn) A method according to claim 8, wherein said selective etching is carried out in a spin etcher.
- 13. (Withdrawn) A method according to claim 8, wherein said selective etching is carried out in a drip etcher.
- 14. (Currently amended) An etching solution according to Claim <u>17</u> 1, wherein the amount of said water is 6.4 -20 % by weight.
- 15. (Canceled)
- 16. (Canceled)
- 17. (Previously presented) An etching solution for the production of integrated circuits consisting essentially of
 - 5-20% by weight hydrofluoric acid, a solvent mixture consisting essentially of at least two of ethylene glycol, propylene glycol, ethanol, and glycerol, and
 - 1-20 % by weight water.
- 18. (Previously presented) An etching solution according to claim 17, wherein the amount of hydrofluoric acid is 10- 20% by weight.
- 19. (Previously presented) An etching solution according to claim 17, wherein the amount of hydrofluoric acid is 15- 20% by weight.